UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 6,794,711 B2
DATED : September 21, 2004
INVENTOR(S) : Kang et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 4,
Line 36, "the select transistor" should read -- the select transistor II. --.

Column 5,
Line 56, "transistor II. The" should read -- transistor III. The --.

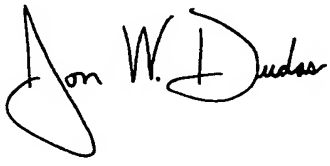
Column 6,
Line 43, "transistor m. At" should read -- transistor III. At --.

Column 7,
Line 12, "transistor m is" should read -- transistor III is --.
Line 23, "transistor m. Therefore," should read -- transistor III. Therefore, --.
Line 33, "transistor m. Their" should read -- transistor III. Their --.
Line 60, "transistor m is" should read -- transistor III is --.

Column 18,
Line 43, "among sidewall, of" should read -- among sidewalls of --.
Line 46, "gate structure an the" should read -- gate structure on the --.

Signed and Sealed this

Twelfth Day of July, 2005



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Director of the United States Patent and Trademark Office